

AMENDMENTS

In the claims:

Please cancel claims ~~11-16~~ without prejudice.

Please amend claim 1 and 17 as follows.

Sub C1
A1
~~1. (Amended) A semiconductor-on-insulator (SOI) structure having;
a semiconductor substrate;
a leaky, thermally conductive insulator material (LTCIM) layer disposed
directly on the semiconductor substrate; and
a semiconductor layer disposed directly on the LTCIM layer; and
active regions defined in the semiconductor layer by isolation trenches and
the LTCIM layer.~~

Sub C1
A2
~~17. (Amended) A semiconductor-on-insulator (SOI) structure having;
a semiconductor substrate;
a leaky, thermally conductive material (LTCIM) layer disposed directly on the
semiconductor substrate;
a semiconductor layer disposed directly on the (LTCIM) layer;
a gate defining a channel interposed between a source and a drain formed
within an active region of the SOI structure; and
the active region defined in the semiconductor layer by isolation trenches and
the LTCIM layer.~~

Marked-up versions of the amended claims appear in an Appendix A.

Please add claims 18 and 19 as follows:

Sub C1
A3
~~18. (Added) A semiconductor-on-insulator (SOI) structure having;
a semiconductor substrate;~~